Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	97
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000l-1fg144

Spine Access

The physical location of each spine is identified by the letter T (top) or B (bottom) and an accompanying number (T*n* or B*n*). The number *n* indicates the horizontal location of the spine; 1 refers to the first spine on the left side of the die. Since there are six chip spines in each spine tree, there are up to six spines available for each combination of T (or B) and *n* (for example, six T1 spines). Similarly, there are three quadrant spines available for each combination of T (or B) and *n* (for example, four T1 spines), as shown in Figure 3-7.

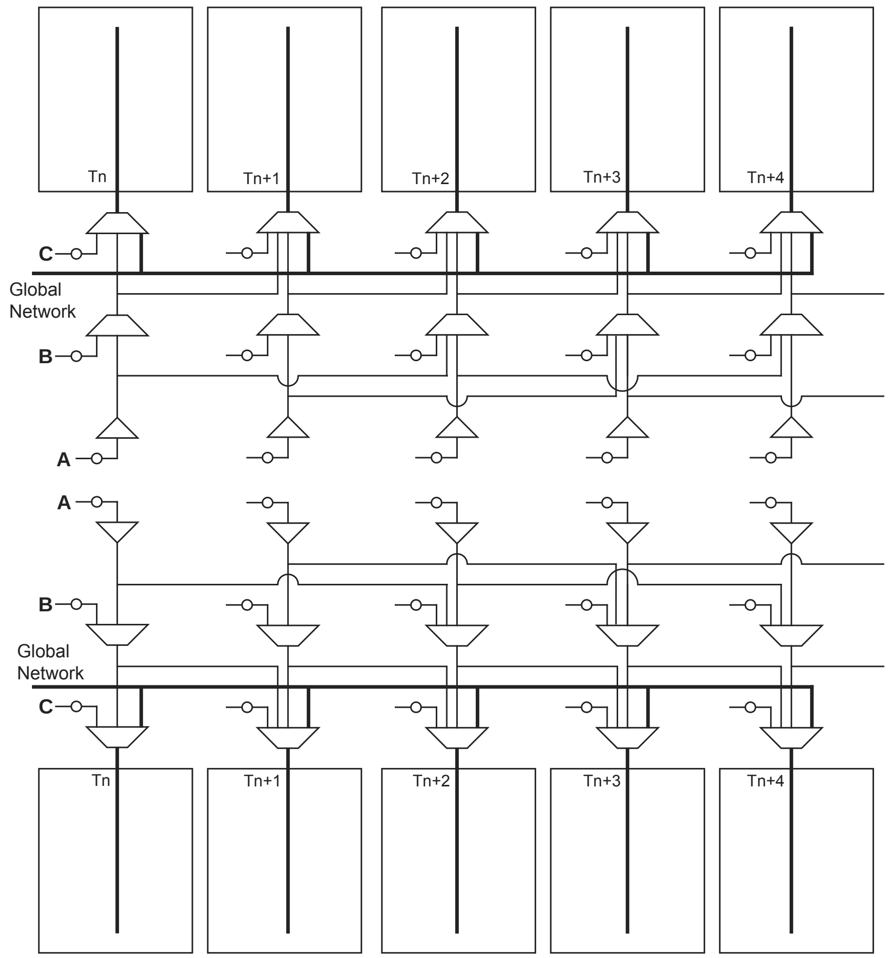


Figure 3-7 **• Chip Global Aggregation**

A spine is also called a local clock network, and is accessed by the dedicated global MUX architecture. These MUXes define how a particular spine is driven. Refer to Figure 3-8 on page 60 for the global MUX architecture. The MUXes for each chip global spine are located in the middle of the die. Access to the top and bottom chip global spine is available from the middle of the die. There is no control dependency between the top and bottom spines. If a top spine, T1, of a chip global network is assigned to a net, B1 is not wasted and can be used by the global clock network. The signal assigned only to the top or bottom spine cannot access the middle two rows of the architecture. However, if a spine is using the top and bottom at the same time (T1 and B1, for instance), the previous restriction is lifted.

The MUXes for each quadrant global spine are located in the north and south sides of the die. Access to the top and bottom quadrant global spines is available from the north and south sides of the die. Since the MUXes for quadrant spines are located in the north and south sides of the die, you should not try to drive T1 and B1 quadrant spines from the same signal.

Implementing EXTFB in ProASIC3/E Devices

When the external feedback (EXTFB) signal of the PLL in the ProASIC3/E devices is implemented, the phase detector of the PLL core receives the reference clock (CLKA) and EXTFB as inputs. EXTFB must be sourced as an INBUF macro and located at the global/chip clock location associated with the target PLL by Designer software. EXTFB cannot be sourced from the FPGA fabric.

The following example shows CLKA and EXTFB signals assigned to two global I/Os in the same global area of ProASIC3E device.

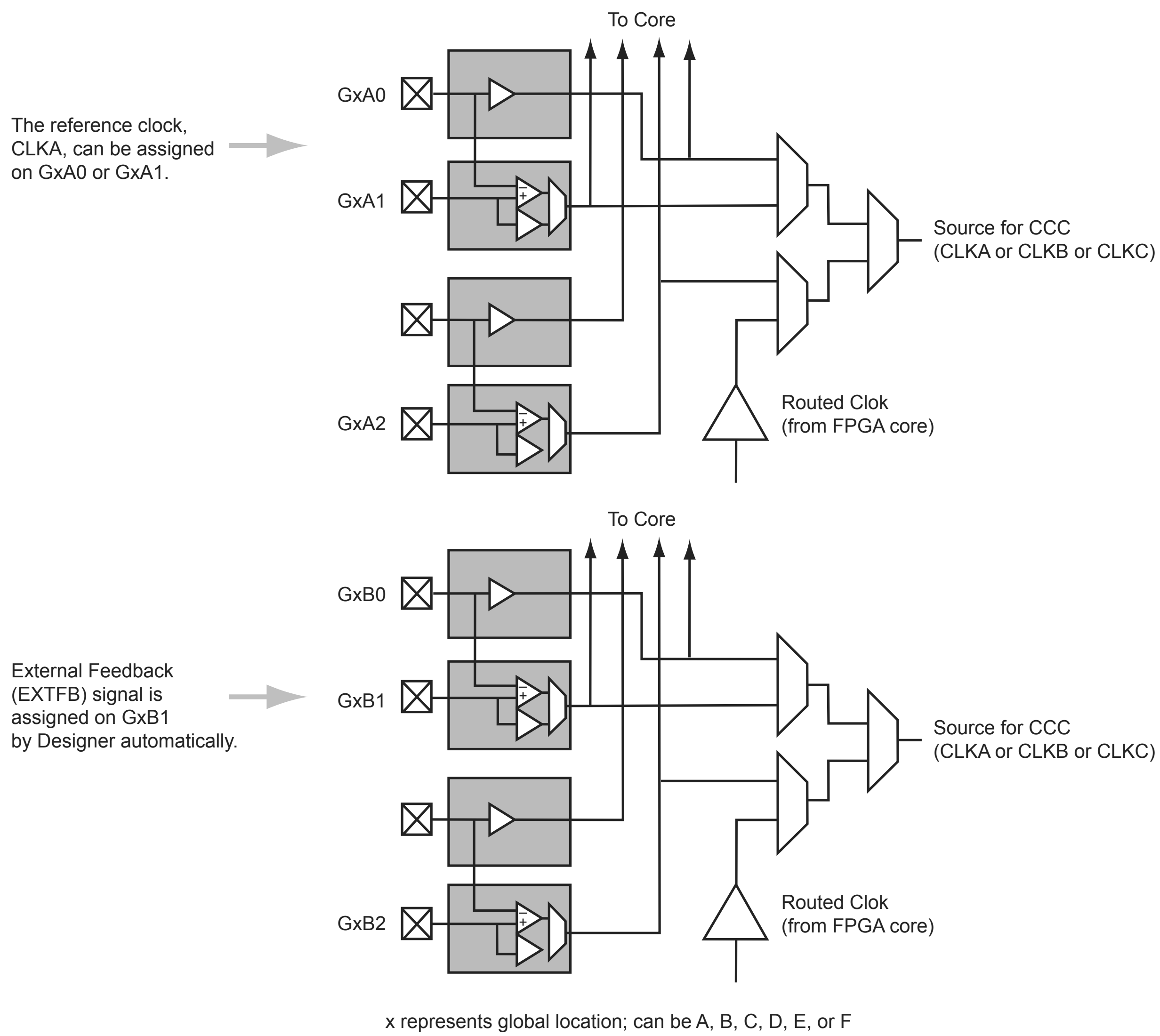
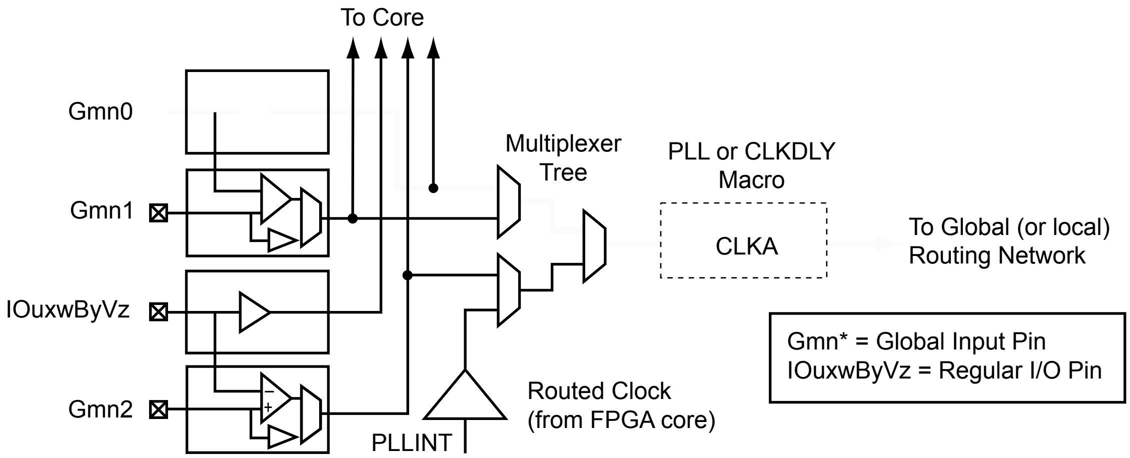


Figure 4-5 • **CLKA and EXTFB Assigned to Global I/Os**



Note: *Fusion CCCs have additional source selections (RCOSC, XTAL).*

Figure 4-9 **• Illustration of Hardwired I/O (global input pins) Usage for IGLOO and ProASIC3 devices 60 k Gates and Larger**

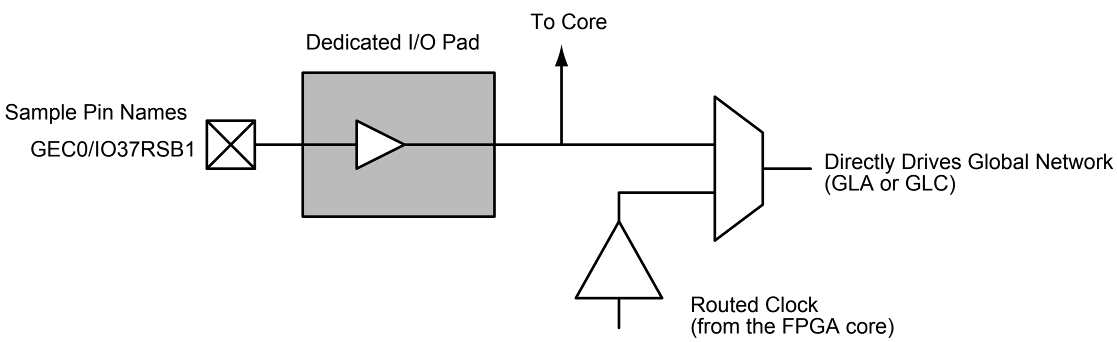


Figure 4-10 **• Illustration of Hardwired I/O (global input pins) Usage for IGLOO and ProASIC3 devices 30 k Gates and Smaller**

Fusion CCC Locations

Fusion devices have six CCCs: one in each of the four corners and one each in the middle of the east and west sides of the device (Figure 4-17 and Figure 4-18). The device can have one integrated PLL in the middle of the west side of the device or two integrated PLLs in the middle of the east and west sides of the device (middle right and middle left).

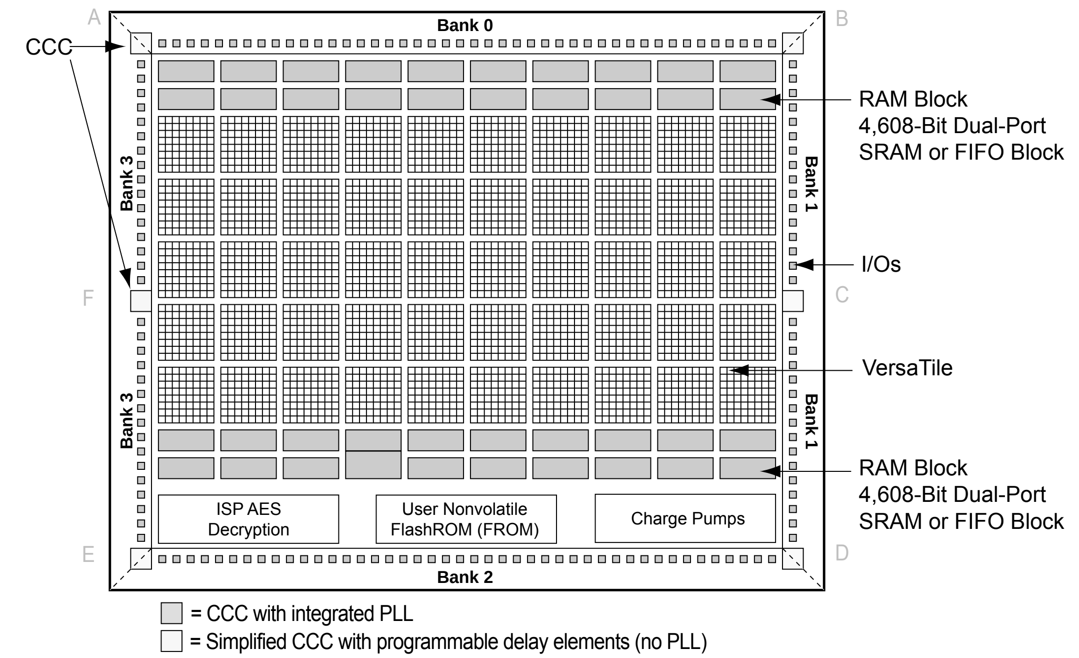


Figure 4-17 **• CCC Locations in Fusion Family Devices (AFS090, AFS250, M1AFS250)**

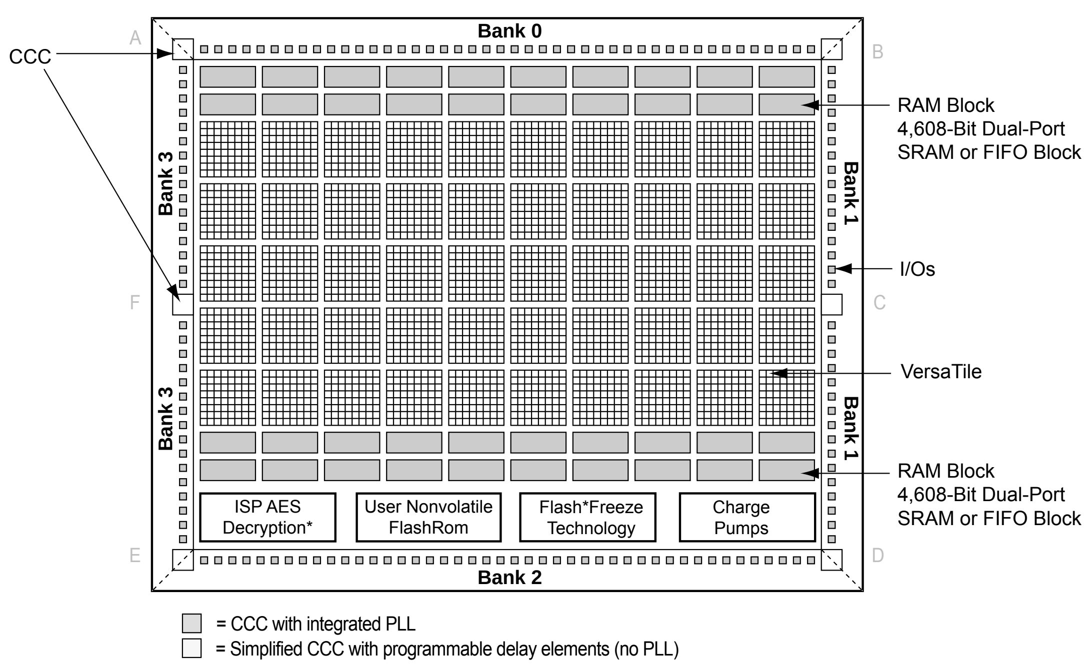


Figure 4-18 **• CCC Locations in Fusion Family Devices (except AFS090, AFS250, M1AFS250)**

```
DLYGLC[4:0]     00000
DLYYB[4:0]      00000
DLYYC[4:0]      00000
VCOSEL[2:0]     100

Primary Clock Frequency 33.000
Primary Clock Phase Shift 0.000
Primary Clock Output Delay from CLKA 1.695

Secondary1 Clock Frequency 40.000
Secondary1 Clock Phase Shift 0.000
Secondary1 Clock Global Output Delay from CLKB 0.200

Secondary2 Clock Frequency 50.000
Secondary2 Clock Phase Shift 0.000
Secondary2 Clock Global Output Delay from CLKC 0.200

######################################
# Dynamic Stream Data
######################################
--------------------------------------
|NAME    |SDIN     |VALUE   |TYPE     |
--------------------------------------
|FINDIV  |[6:0]    |0000101 |EDIT     |
|FBDIV   |[13:7]   |0100000 |EDIT     |
|OADIV   |[18:14]  |00100   |EDIT     |
|OBDIV   |[23:19]  |00000   |EDIT     |
|OCDIV   |[28:24]  |00000   |EDIT     |
|OAMUX   |[31:29]  |100     |EDIT     |
|OBMUX   |[34:32]  |000     |EDIT     |
|OCMUX   |[37:35]  |000     |EDIT     |
|FBSEL   |[39:38]  |01      |EDIT     |
|FBDLY   |[44:40]  |00000   |EDIT     |
|XDLYSEL |[45]     |0       |EDIT     |
|DLYGLA  |[50:46]  |00000   |EDIT     |
|DLYGLB  |[55:51]  |00000   |EDIT     |
|DLYGLC  |[60:56]  |00000   |EDIT     |
|DLYYB   |[65:61]  |00000   |EDIT     |
|DLYYC   |[70:66]  |00000   |EDIT     |
|STATASEL|[71]     |X       |MASKED   |
|STATBSEL|[72]     |X       |MASKED   |
|STATCSEL|[73]     |X       |MASKED   |
|VCOSEL  |[76:74]  |100     |EDIT     |
|DYNASEL |[77]     |X       |MASKED   |
|DYNBSEL |[78]     |X       |MASKED   |
|DYNCSEL |[79]     |X       |MASKED   |
|RESETEN |[80]     |1       |READONLY |
```

Below is the resultant Verilog HDL description of a legal dynamic PLL core configuration generated by SmartGen:

```
module dyn_pll_macro(POWERDOWN, CLKA, LOCK, GLA, GLB, GLC, SDIN, SCLK, SSHIFT, SUPDATE,
  MODE, SDOUT, CLKB, CLKC);

input POWERDOWN, CLKA;
output  LOCK, GLA, GLB, GLC;
input  SDIN, SCLK, SSHIFT, SUPDATE, MODE;
output  SDOUT;
input  CLKB, CLKC;

  wire VCC, GND;

  VCC VCC_1_net(.Y(VCC));
  GND GND_1_net(.Y(GND));
```

FlashROM Generation and Instantiation in the Design

The SmartGen core generator, available in Libero SoC and Designer, is the only tool that can be used to generate the FlashROM content. SmartGen has several user-friendly features to help generate the FlashROM contents. Instead of selecting each byte and assigning values, you can create a region within a page, modify the region, and assign properties to that region. The FlashROM user interface, shown in Figure 5-10, includes the configuration grid, existing regions list, and properties field. The properties field specifies the region-specific information and defines the data used for that region. You can assign values to the following properties:

1. Static Fixed Data—Enables you to fix the data so it cannot be changed during programming time. This option is useful when you have fixed data stored in this region, which is required for the operation of the design in the FPGA. Key storage is one example.
2. Static Modifiable Data—Select this option when the data in a particular region is expected to be static data (such as a version number, which remains the same for a long duration but could conceivably change in the future). This option enables you to avoid changing the value every time you enter new data.
3. Read from File—This provides the full flexibility of FlashROM usage to the customer. If you have a customized algorithm for generating the FlashROM data, you can specify this setting. You can then generate a text file with data for as many devices as you wish to program, and load that into the FlashPoint programming file generation software to get programming files that include all the data. SmartGen will optionally pass the location of the file where the data is stored if the file is specified in SmartGen. Each text file has only one type of data format (binary, decimal, hex, or ASCII text). The length of each data file must be shorter than or equal to the selected region length. If the data is shorter than the selected region length, the most significant bits will be padded with 0s. For multiple text files for multiple regions, the first lines are for the first device. In SmartGen, **Load Sim. Value From File** allows you to load the first device data in the MEM file for simulation.
4. Auto Increment/Decrement—This scenario is useful when you specify the contents of FlashROM for a large number of devices in a series. You can specify the step value for the serial number and a maximum value for inventory control. During programming file generation, the actual number of devices to be programmed is specified and a start value is fed to the software.

Figure 5-10 **• SmartGen GUI of the FlashROM**

SRAM Usage

The following descriptions refer to the usage of both RAM4K9 and RAM512X18.

Clocking

The dual-port SRAM blocks are only clocked on the rising edge. SmartGen allows falling-edge-triggered clocks by adding inverters to the netlist, hence achieving dual-port SRAM blocks that are clocked on either edge (rising or falling). For dual-port SRAM, each port can be clocked on either edge and by separate clocks by port. Note that for Automotive ProASIC3, the same clock, with an inversion between the two clock pins of the macro, should be used in design to prevent errors during compile.

Low power flash devices support inversion (bubble-pushing) throughout the FPGA architecture, including the clock input to the SRAM modules. Inversions added to the SRAM clock pin on the design schematic or in the HDL code will be automatically accounted for during design compile without incurring additional delay in the clock path.

The two-port SRAM can be clocked on the rising or falling edge of WCLK and RCLK.

If negative-edge RAM and FIFO clocking is selected for memory macros, clock edge inversion management (bubble-pushing) is automatically used within the development tools, without performance penalty.

Modes of Operation

There are two read modes and one write mode:

- Read Nonpipelined (synchronous—1 clock edge): In the standard read mode, new data is driven onto the RD bus in the same clock cycle following RA and REN valid. The read address is registered on the read port clock active edge, and data appears at RD after the RAM access time. Setting PIPE to OFF enables this mode.
- Read Pipelined (synchronous—2 clock edges): The pipelined mode incurs an additional clock delay from address to data but enables operation at a much higher frequency. The read address is registered on the read port active clock edge, and the read data is registered and appears at RD after the second read clock edge. Setting PIPE to ON enables this mode.
- Write (synchronous—1 clock edge): On the write clock active edge, the write data is written into the SRAM at the write address when WEN is HIGH. The setup times of the write address, write enables, and write data are minimal with respect to the write clock.

RAM Initialization

Each SRAM block can be individually initialized on power-up by means of the JTAG port using the UJTAG mechanism. The shift register for a target block can be selected and loaded with the proper bit configuration to enable serial loading. The 4,608 bits of data can be loaded in a single operation.

FIFO Features

The FIFO4KX18 macro is created by merging the RAM block with dedicated FIFO logic (Figure 6-6 on page 158). Since the FIFO logic can only be used in conjunction with the memory block, there is no separate FIFO controller macro. As with the RAM blocks, the FIFO4KX18 nomenclature does not refer to a possible aspect ratio, but rather to the deepest possible data depth and the widest possible data width. FIFO4KX18 can be configured into the following aspect ratios: 4,096×1, 2,048×2, 1,024×4, 512×9, and 256×18. In addition to being fully synchronous, the FIFO4KX18 also has the following features:

- Four FIFO flags: Empty, Full, Almost-Empty, and Almost-Full
- Empty flag is synchronized to the read clock
- Full flag is synchronized to the write clock
- Both Almost-Empty and Almost-Full flags have programmable thresholds
- Active-low asynchronous reset
- Active-low block enable
- Active-low write enable
- Active-high read enable
- Ability to configure the FIFO to either stop counting after the empty or full states are reached or to allow the FIFO counters to continue

Example of RAM Initialization

This section of the document presents a sample design in which a 4×4 RAM block is being initialized through the JTAG port. A test feature has been implemented in the design to read back the contents of the RAM after initialization to verify the procedure.

The interface block of this example performs two major functions: initialization of the RAM block and running a test procedure to read back the contents. The clock output of the interface is either the write clock (for initialization) or the read clock (for reading back the contents). The Verilog code for the interface block is included in the "Sample Verilog Code" section on page 167.

For simulation purposes, users can declare the input ports of the UJTAG macro for easier assignment in the testbench. However, the UJTAG input ports should not be declared on the top level during synthesis. If the input ports of the UJTAG are declared during synthesis, the synthesis tool will instantiate input buffers on these ports. The input buffers on the ports will cause Compile to fail in Designer.

Figure 6-10 shows the simulation results for the initialization step of the example design.

The CLK_OUT signal, which is the clock output of the interface block, is the inverted DR_UPDATE output of the UJTAG macro. It is clear that it gives sufficient time (while the TAP Controller is in the Data Register Update state) for the write address and data to become stable before loading them into the RAM block.

Figure 6-11 presents the test procedure of the example. The data read back from the memory block matches the written data, thus verifying the design functionality.

Figure 6-10 **• Simulation of Initialization Step**

Figure 6-11 **• Simulation of the Test Procedure of the Example**

I/O Bank Structure

Low power flash device I/Os are divided into multiple technology banks. The number of banks is device-dependent. The IGLOOe, ProASIC3EL, and ProASIC3E devices have eight banks (two per side); and IGLOO, ProASIC3L, and ProASIC3 devices have two to four banks. Each bank has its own V**CCI** power supply pin. Multiple I/O standards can co-exist within a single I/O bank.

In IGLOOe, ProASIC3EL, and ProASIC3E devices, each I/O bank is subdivided into VREF minibanks. These are used by voltage-referenced I/Os. VREF minibanks contain 8 to 18 I/Os. All I/Os in a given minibank share a common VREF line (only one VREF pin is needed per VREF minibank). Therefore, if an I/O in a VREF minibank is configured as a VREF pin, the remaining I/Os in that minibank will be able to use the voltage assigned to that pin. If the location of the VREF pin is selected manually in the software, the user must satisfy VREF rules (refer to the "I/O Software Control in Low Power Flash Devices" section on page 251). If the user does not pick the VRE_F pin manually, the software automatically assigns it.

Figure 7-3 is a snapshot of a section of the I/O ring, showing the basic elements of an I/O tile, as viewed from the Designer place-and-route tool's MultiView Navigator (MVN).

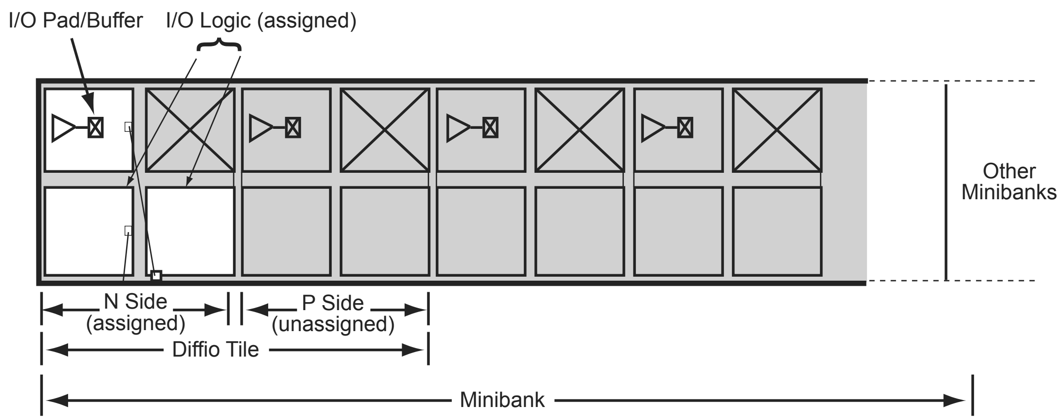


Figure 7-3 **• Snapshot of an I/O Tile**

Low power flash device I/Os are implemented using two tile types: I/O and differential I/O (diffio).

The diffio tile is built up using two I/O tiles, which form an I/O pair (P side and N side). These I/O pairs are used according to differential I/O standards. Both the P and N sides of the diffio tile include an I/O buffer and two I/O logic blocks (auxiliary and main logic).

Every minibank (E devices only) is built up from multiple diffio tiles. The number of the minibank depends on the different-size dies. Refer to the "I/O Architecture" section on page 181 for an illustration of the minibank structure.

Figure 7-4 on page 183 shows a simplified diagram of the I/O buffer circuitry. The Output Enable signal (OE) enables the output buffer to pass the signal from the core logic to the pin. The output buffer contains ESD protection circuitry, an n-channel transistor that shunts all ESD surges (up to the limit of the device ESD specification) to GND. This transistor also serves as an output pull-down resistor.

Each output buffer also contains programmable slew rate, drive strength, programmable power-up state (pull-up/-down resistor), hot-swap, 5 V tolerance, and clamp diode control circuitry. Multiple flash switches (not shown in Figure 7-4 on page 183) are programmed by user selections in the software to activate different I/O features.

Example: For a bus consisting of 20 equidistant loads, the terminations given in EQ 1 provide the required differential voltage, in worst-case industrial operating conditions, at the farthest receiver:

$R_S = 60\ \Omega$, $R_T = 70\ \Omega$, given $Z_O = 50\ \Omega$ (2") and $Z_{stub} = 50\ \Omega$ (~1.5").

EQ 1

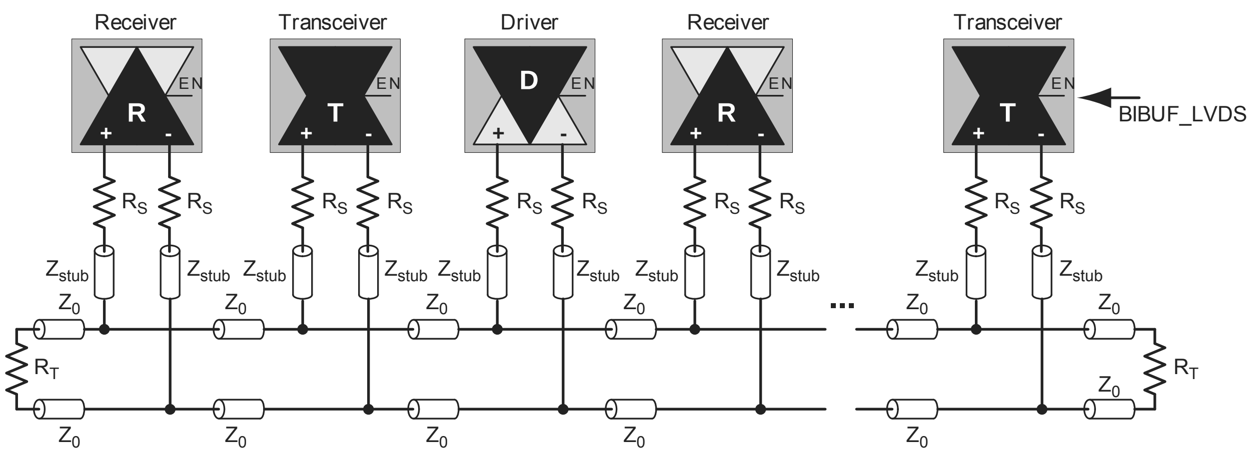


Figure 7-8 **• A B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers**

Table 7-8 • **Hot-Swap Level 1**

Description	Cold-swap
Power Applied to Device	No
Bus State	–
Card Ground Connection	–
Device Circuitry Connected to Bus Pins	–
Example Application	System and card with Microsemi FPGA chip are powered down, and the card is plugged into the system. Then the power supplies are turned on for the system but not for the FPGA on the card.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices: Compliant Other IGLOO/ProASIC3 devices: Compliant if bus switch used to isolate FPGA I/Os from rest of system IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode.

Table 7-9 • **Hot-Swap Level 2**

Description	Hot-swap while reset
Power Applied to Device	Yes
Bus State	Held in reset state
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	–
Example Application	In the PCI hot-plug specification, reset control circuitry isolates the card busses until the card supplies are at their nominal operating levels and stable.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices, all IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode. Other IGLOO/ProASIC3 devices: Compliant

Table 7-12 **• I/O Hot-Swap and 5 V Input Tolerance Capabilities in IGLOO and ProASIC3 Devices**

I/O Assignment	Clamp Diode [1]		Hot Insertion		5 V Input Tolerance [2]		Input and Output Buffer
	AGL030 and A3P030	Other IGLOO and ProASIC3 Devices	AGL015 and AGL030	Other IGLOO Devices and All ProASIC3	AGL030 and A3P030	Other IGLOO and ProASIC3 Devices	
3.3 V LVTTL/LVCMOS	No	Yes	Yes	No	Yes [2]	Yes [2]	Enabled/Disabled
3.3 V PCI, 3.3 V PCI-X	N/A	Yes	N/A	No	N/A	Yes [2]	Enabled/Disabled
LVCMOS 2.5 V [5]	No	Yes	Yes	No	Yes [2]	Yes [4]	Enabled/Disabled
LVCMOS 2.5 V/5.0 V [6]	N/A	Yes	N/A	No	N/A	Yes [4]	Enabled/Disabled
LVCMOS 1.8 V	No	Yes	Yes	No	No	No	Enabled/Disabled
LVCMOS 1.5 V	No	Yes	Yes	No	No	No	Enabled/Disabled
Differential, LVDS/ B-LVDS/M-LVDS/LVPECL	N/A	Yes	N/A	No	N/A	No	Enabled/Disabled

Notes:

1. *The clamp diode is always off for the AGL030 and A3P030 device and always active for other IGLOO and ProASIC3 devices.*
2. *Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.*
3. *Refer to Table 7-8 on page 189 to Table 7-11 on page 190 for device-compliant information.*
4. *Can be implemented with an external resistor and an internal clamp diode.*
5. *The LVCMOS 2.5 V I/O standard is supported by the 30 k gate devices only; select the LVCMOS25 macro.*
6. *The LVCMOS 2.5 V / 5.0 V I/O standard is supported by all IGLOO and ProASIC3 devices except 30K gate devices; select the LVCMOS5 macro.*

***Table 7-13* • Comparison Table for 5 V–Compliant Receiver Solutions**

Solution	Board Components	Speed	Current Limitations
1	Two resistors	Low to High[1]	Limited by transmitter's drive strength
2	Resistor and Zener 3.3 V	Medium	Limited by transmitter's drive strength
3	Bus switch	High	N/A
4	Minimum resistor value[2,3,4,5] R = 47 Ω at T_J = 70°C R = 150 Ω at T_J = 85°C R = 420 Ω at T_J = 100°C	Medium	Maximum diode current at 100% duty cycle, signal constantly at 1 52.7 mA at T_J = 70°C / 10-year lifetime 16.5 mA at T_J = 85°C / 10-year lifetime 5.9 mA at T_J = 100°C / 10-year lifetime For duty cycles other than 100%, the currents can be increased by a factor of 1 / (duty cycle). Example: 20% duty cycle at 70°C Maximum current = (1 / 0.2) × 52.7 mA = 5 × 52.7 mA = 263.5 mA

Notes:

1. *Speed and current consumption increase as the board resistance values decrease.*
2. *Resistor values ensure I/O diode long-term reliability.*
3. *At 70°C, customers could still use 420 Ω on every I/O.*
4. *At 85°C, a 5 V solution on every other I/O is permitted, since the resistance is lower (150 Ω) and the current is higher. Also, the designer can still use 420 Ω and use the solution on every I/O.*
5. *At 100°C, the 5 V solution on every I/O is permitted, since 420 Ω are used to limit the current to 5.9 mA.*

5 V Output Tolerance

IGLOO and ProASIC3 I/Os must be set to 3.3 V LVTTL or 3.3 V LVCMOS mode to reliably drive 5 V TTL receivers. It is also critical that there be NO external I/O pull-up resistor to 5 V, since this resistor would pull the I/O pad voltage beyond the 3.6 V absolute maximum value and consequently cause damage to the I/O.

When set to 3.3 V LVTTL or 3.3 V LVCMOS mode, the I/Os can directly drive signals into 5 V TTL receivers. In fact, VOL = 0.4 V and VOH = 2.4 V in both 3.3 V LVTTL and 3.3 V LVCMOS modes exceeds the VIL = 0.8 V and VIH = 2 V level requirements of 5 V TTL receivers. Therefore, level 1 and level 0 will be recognized correctly by 5 V TTL receivers.

Schmitt Trigger

A Schmitt trigger is a buffer used to convert a slow or noisy input signal into a clean one before passing it to the FPGA. Using Schmitt trigger buffers guarantees a fast, noise-free input signal to the FPGA.

The Schmitt trigger is available for the LVTTL, LVCMOS, and 3.3 V PCI I/O standards.

This feature can be implemented by using a Physical Design Constraints (PDC) command (Table 7-5 on page 179) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

Software-Controlled I/O Attributes

Users may modify these programmable I/O attributes using the I/O Attribute Editor. Modifying an I/O attribute may result in a change of state in Designer. Table 9-2 details which steps have to be re-run as a function of modified I/O attribute.

Table 9-2 **• Designer State (resulting from I/O attribute modification)**

I/O Attribute	Designer States[1]				
	Compile	Layout	Fuse	Timing	Power
Slew Control[2]	No	No	Yes	Yes	Yes
Output Drive (mA)	No	No	Yes	Yes	Yes
Skew Control	No	No	Yes	Yes	Yes
Resistor Pull	No	No	Yes	Yes	Yes
Input Delay	No	No	Yes	Yes	Yes
Schmitt Trigger	No	No	Yes	Yes	Yes
OUT_LOAD	No	No	No	Yes	Yes
COMBINE_REGISTER	Yes	Yes	N/A	N/A	N/A

Notes:

1. *No = Remains the same, Yes = Re-run the step, N/A = Not applicable*
2. *Skew control does not apply to IGLOO nano, IGLOO PLUS, and ProASIC3 nano devices.*
3. *Programmable input delay is applicable only for ProASIC3E, ProASIC3EL, RT ProASIC3, and IGLOOe devices.*

Table 9-3 • PDC I/O Constraints (continued)

Command	Action	Example	Comment
I/O Attribute Constraint			
set_io	Sets the attributes of an I/O	set_io portname [-pinname value] [-fixed value] [-iostd value] [-out_drive value] [-slew value] [-res_pull value] [-schmitt_trigger value] [-in_delay value] [-skew value] [-out_load value] [-register value] set_io IN2 -pinname 28 -fixed yes -iostd LVCMOS15 -out_drive 12 -slew high -RES_PULL None -SCHMITT_TRIGGER Off -IN_DELAY Off –skew off -REGISTER No	If the I/O macro is generic (e.g., INBUF) or technology-specific (INBUF_LVCMOS25), then all I/O attributes can be assigned using this constraint. If the netlist has an I/O macro that specifies one of its attributes, that attribute cannot be changed using this constraint, though other attributes can be changed. Example: OUTBUF_S_24 (low slew, output drive 24 mA) Slew and output drive cannot be changed.
I/O Region Placement Constraints			
define_region	Defines either a rectangular region or a rectilinear region	define_region -name [region_name] -type [region_type] x1 y1 x2 y2 define_region -name test -type inclusive 0 15 2 29	If any number of I/Os must be assigned to a particular I/O region, such a region can be created with this constraint.
assign_region	Assigns a set of macros to a specified region	assign_region [region name] [macro_name...] assign_region test U12	This constraint assigns I/O macros to the I/O regions. When assigning an I/O macro, PDC naming conventions must be followed if the macro name contains special characters; e.g., if the macro name is \\$1I19\\, the correct use of escape characters is \\\\$1I19\\\\.

Note: *Refer to the* Libero SoC User’s Guide *for detailed rules on PDC naming and syntax conventions.*

Automatically Assigning Technologies to I/O Banks

The I/O Bank Assigner (IOBA) tool runs automatically when you run Layout. You can also use this tool from within the MultiView Navigator (Figure 9-17). The IOBA tool automatically assigns technologies and VREF pins (if required) to every I/O bank that does not currently have any technologies assigned to it. This tool is available when at least one I/O bank is unassigned.

To automatically assign technologies to I/O banks, choose I/O Bank Assigner from the **Tools** menu (or click the I/O Bank Assigner's toolbar button, shown in Figure 9-16).

Figure 9-16 **• I/O Bank Assigner's Toolbar Button**

Messages will appear in the Output window informing you when the automatic I/O bank assignment begins and ends. If the assignment is successful, the message "I/O Bank Assigner completed successfully" appears in the Output window, as shown in Figure 9-17.

Figure 9-17 **• I/O Bank Assigner Displays Messages in Output Window**

Programming Voltage (VPUMP) and VJTAG

Low-power flash devices support on-chip charge pumps, and therefore require only a single 3.3 V programming voltage for the VPUMP pin during programming. When the device is not being programmed, the VPUMP pin can be left floating or can be tied (pulled up) to any voltage between 0 V and 3.6 V[2]. During programming, the target board or the FlashPro4/3/3X programmer can provide VPUMP. FlashPro4/3/3X is capable of supplying VPUMP to a single device. If more than one device is to be programmed using FlashPro4/3/3X on a given board, FlashPro4/3/3X should not be relied on to supply the VPUMP voltage. A FlashPro4/3/3X programmer is not capable of providing reliable VJTAG voltage. The board must supply VJTAG voltage to the device and the VJTAG pin of the programmer header must be connected to the device VJTAG pin. Microsemi recommends that VPUMP[3] and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail. Refer to the "Board-Level Considerations" section on page 337 for capacitor requirements.

Low power flash device I/Os support a bank-based, voltage-supply architecture that simultaneously supports multiple I/O voltage standards (Table 13-2). By isolating the JTAG power supply in a separate bank from the user I/Os, low power flash devices provide greater flexibility with supply selection and simplify power supply and printed circuit board (PCB) design. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Microsemi recommends that TCK be tied to GND through a 200 ohm to 1 Kohm resistor. This prevents a possible totempole current on the input buffer stage. For TDI, TMS, and TRST pins, the devices provide an internal nominal 10 Kohm pull-up resistor. During programming, all I/O pins, except for JTAG interface pins, are tristated and weakly pulled up to VCCI. This isolates the part and prevents the signals from floating. The JTAG interface pins are driven by the FlashPro4/3/3X during programming, including the TRST pin, which is driven HIGH.

***Table 13-2* • Power Supplies**

Power Supply	Programming Mode	Current during Programming
VCC	1.2 V / 1.5 V	< 70 mA
VCCI	1.2 V / 1.5 V / 1.8 V / 2.5 V / 3.3 V (bank-selectable)	I/Os are weakly pulled up.
VJTAG	1.2 V / 1.5 V / 1.8 V / 2.5 V / 3.3 V	< 20 mA
VPUMP	3.15 V to 3.45 V	< 80 mA

Note: All supply voltages should be at 1.5 V or higher, regardless of the setting during normal operation, except for IGLOO nano, where 1.2 V VCC and VJTAG programming is allowed.

Nonvolatile Memory (NVM) Programming Voltage

SmartFusion and Fusion devices need stable VCCNVM/VCCENVM[3] (1.5 V power supply to the embedded nonvolatile memory blocks) and VCCOSC/VCCROSC[4] (3.3 V power supply to the integrated RC oscillator). The tolerance of VCCNVM/VCCENVM is ± 5% and VCCOSC/VCCROSC is ± 5%.

Unstable supply voltage on these pins can cause an NVM programming failure due to NVM page corruption. The NVM page can also be corrupted if the NVM reset pin has noise. This signal must be tied off properly.

Microsemi recommends installing the following capacitors[5] on the VCCNVM/VCCENVM and VCCOSC/VCCROSC pins:

- Add one bypass capacitor of 10 µF for each power supply plane followed by an array of decoupling capacitors of 0.1 µF.
- Add one 0.1 µF capacitor near each pin.

2. *During sleep mode in IGLOO devices connect VPUMP to GND.*
3. *VPUMP has to be quiet for successful programming. Therefore VPUMP must be separate and required capacitors must be installed close to the FPGA VPUMP pin.*
4. *VCCROSC is for SmartFusion.*
5. *The capacitors cannot guarantee reliable operation of the device if the board layout is not done properly.*

IEEE 1532 (JTAG) Interface

The supported industry-standard IEEE 1532 programming interface builds on the IEEE 1149.1 (JTAG) standard. IEEE 1532 defines the standardized process and methodology for ISP. Both silicon and software issues are addressed in IEEE 1532 to create a simplified ISP environment. Any IEEE 1532 compliant programmer can be used to program low power flash devices. Device serialization is not supported when using the IEEE1532 standard. Refer to the standard for detailed information about IEEE 1532.

Security

Unlike SRAM-based FPGAs that require loading at power-up from an external source such as a microcontroller or boot PROM, Microsemi nonvolatile devices are live at power-up, and there is no bitstream required to load the device when power is applied. The unique flash-based architecture prevents reverse engineering of the programmed code on the device, because the programmed data is stored in nonvolatile memory cells. Each nonvolatile memory cell is made up of small capacitors and any physical deconstruction of the device will disrupt stored electrical charges.

Each low power flash device has a built-in 128-bit Advanced Encryption Standard (AES) decryption core, except for the 30 k gate devices and smaller. Any FPGA core or FlashROM content loaded into the device can optionally be sent as encrypted bitstream and decrypted as it is loaded. This is particularly suitable for applications where device updates must be transmitted over an unsecured network such as the Internet. The embedded AES decryption core can prevent sensitive data from being intercepted (Figure 13-1 on page 331). A single 128-bit AES Key (32 hex characters) is used to encrypt FPGA core programming data and/or FlashROM programming data in the Microsemi tools. The low power flash devices also decrypt with a single 128-bit AES Key. In addition, low power flash devices support a Message Authentication Code (MAC) for authentication of the encrypted bitstream on-chip. This allows the encrypted bitstream to be authenticated and prevents erroneous data from being programmed into the device. The FPGA core, FlashROM, and Flash Memory Blocks (FBs), in Fusion only, can be updated independently using a programming file that is AES-encrypted (cipher text) or uses plain text.

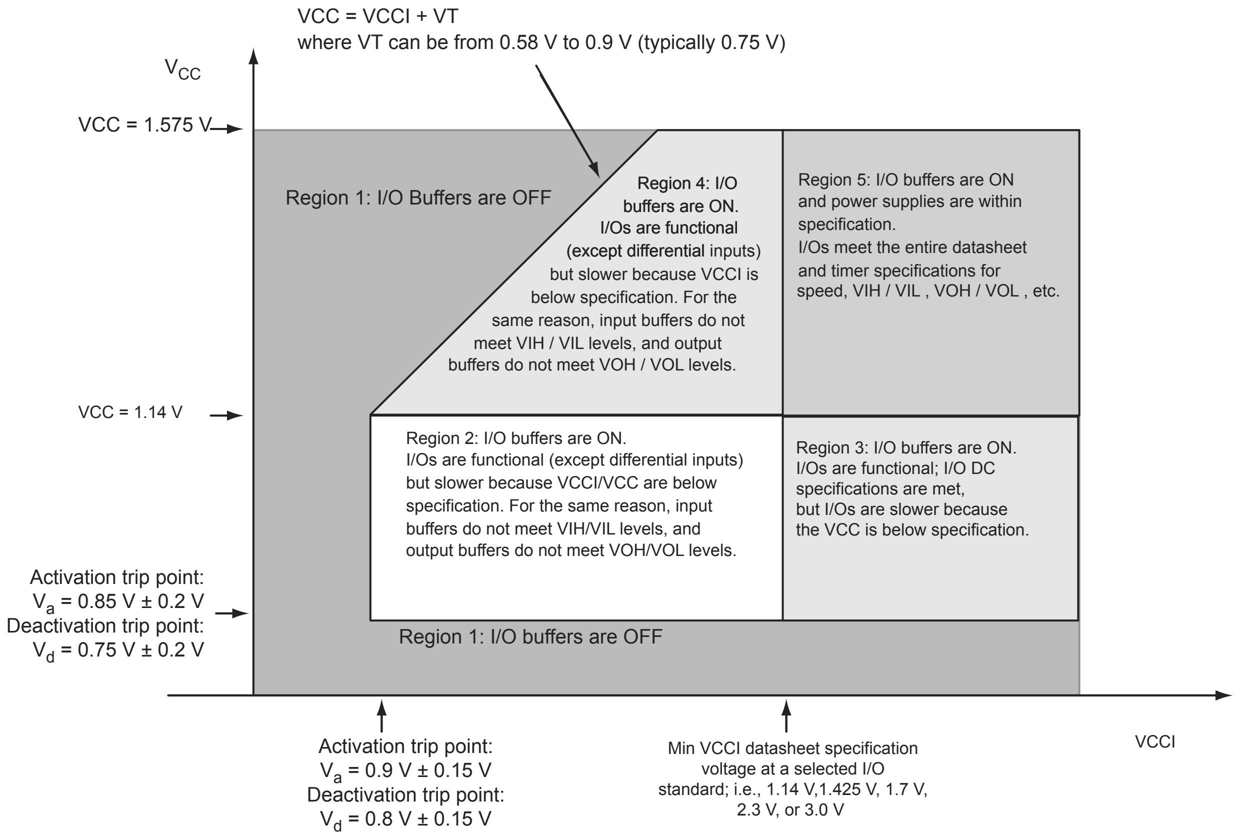


Figure 18-5 **• I/O State as a Function of VCCI and VCC Voltage Levels for IGLOO V2, IGLOO nano V2, IGLOO PLUS V2, and ProASIC3L Devices Running at VCC = 1.2 V ± 0.06 V**

The following devices and families do not support cold-sparing:

- IGLOO: AGL060, AGL125, AGL250, AGL600, AGL1000
- ProASIC3: A3P060, A3P125, A3P250, A3P400, A3P600, A3P1000
- ProASIC3L: A3P250L, A3P600L, A3P1000L
- Military ProASIC3: A3P1000

Hot-Swapping

Hot-swapping is the operation of hot insertion or hot removal of a card in a powered-up system. The I/Os need to be configured in hot-insertion mode if hot-swapping compliance is required. For more details on the levels of hot-swap compatibility in low power flash devices, refer to the "Hot-Swap Support" section in the I/O Structures chapter of the user's guide for the device you are using.

The following devices and families support hot-swapping:

- IGLOO: AGL015 and AGL030
- All IGLOO nano
- All IGLOO PLUS
- All IGLOOe
- ProASIC3L: A3PE3000L
- ProASIC3: A3P015 and A3P030
- All ProASIC3 nano
- All ProASIC3E
- Military ProASIC3EL: A3PE600L and A3PE3000L
- RT ProASIC3: RT3PE600L and RT3PE3000L

The following devices and families do not support hot-swapping:

- IGLOO: AGL060, AGL125, AGL250, AGL400, AGL600, AGL1000
- ProASIC3: A3P060, A3P125, A3P250, A3P400, A3P600, A3P1000
- ProASIC3L: A3P250L, A3P600L, A3P1000L
- Military ProASIC3: A3P1000

Conclusion

Microsemi's low power flash FPGAs provide an excellent programmable logic solution for a broad range of applications. In addition to high performance, low cost, security, nonvolatility, and single chip, they are live at power-up (meet Level 0 of the LAPU classification) and offer clear and easy-to-use power-up/-down characteristics. Unlike SRAM FPGAs, low power flash devices do not require any specific power-up/-down sequencing and have extremely low power-up inrush current in any power-up sequence. Microsemi low power flash FPGAs also support both cold-sparing and hot-swapping for applications requiring these capabilities.